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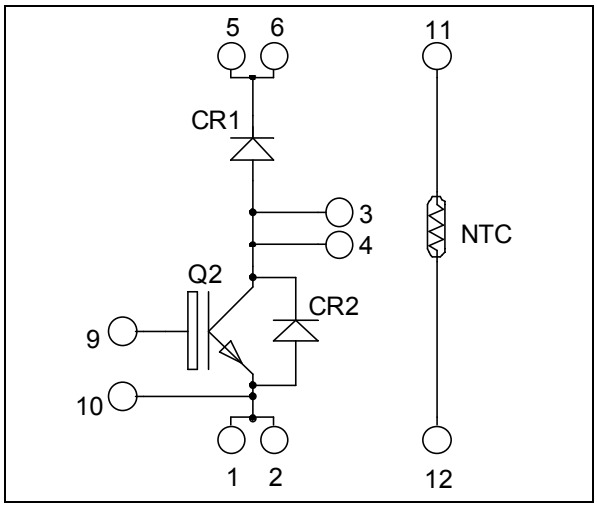
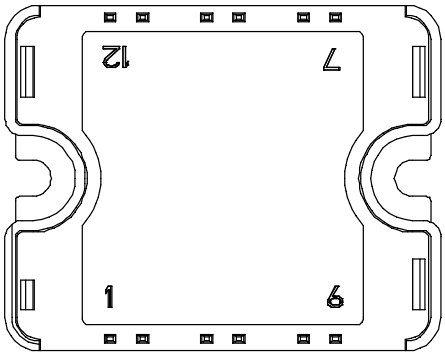
APTGF100DA120T1G

Boost chopper NPT IGBT Power Module

V_{CES} = 1200V
I_C = 100A* @ Tc = 80°C





Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	130*	A
		T_C = 80°C	100*	
I_{CM}	Pulsed Collector Current	T_C = 25°C	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	735	W
RBSOA	Reverse Bias Safe Operating Area	T_J = 150°C	200A @ 1150V	

Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				250	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 100A	T_j = 25°C		3.2	3.7	V
			T_j = 125°C		3.9		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 4mA		4.5	5.5	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			6.5		nF
C_{oes}	Output Capacitance				1		
C_{res}	Reverse Transfer Capacitance				0.5		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 5.6Ω			120		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				310		
T_f	Fall Time				20		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 5.6Ω			130		ns
T_r	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				360		
T_f	Fall Time				30		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{Bus} = 600V I_C = 100A R_G = 5.6Ω	T_j = 125°C		12		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		5		

Chopper diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V	T_j = 25°C			100	µA
			T_j = 125°C			500	
I_F	DC Forward Current		Tc = 90°C		100		A
V_F	Diode Forward Voltage	I_F = 100A			2.4	3	V
		I_F = 150A			2.7		
		I_F = 100A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 100A V_R = 800V di/dt =200A/µs	T_j = 25°C		385		ns
			T_j = 125°C		480		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		1055		nC
			T_j = 125°C		5240		

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.19	°C/W
			Diode			0.55	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

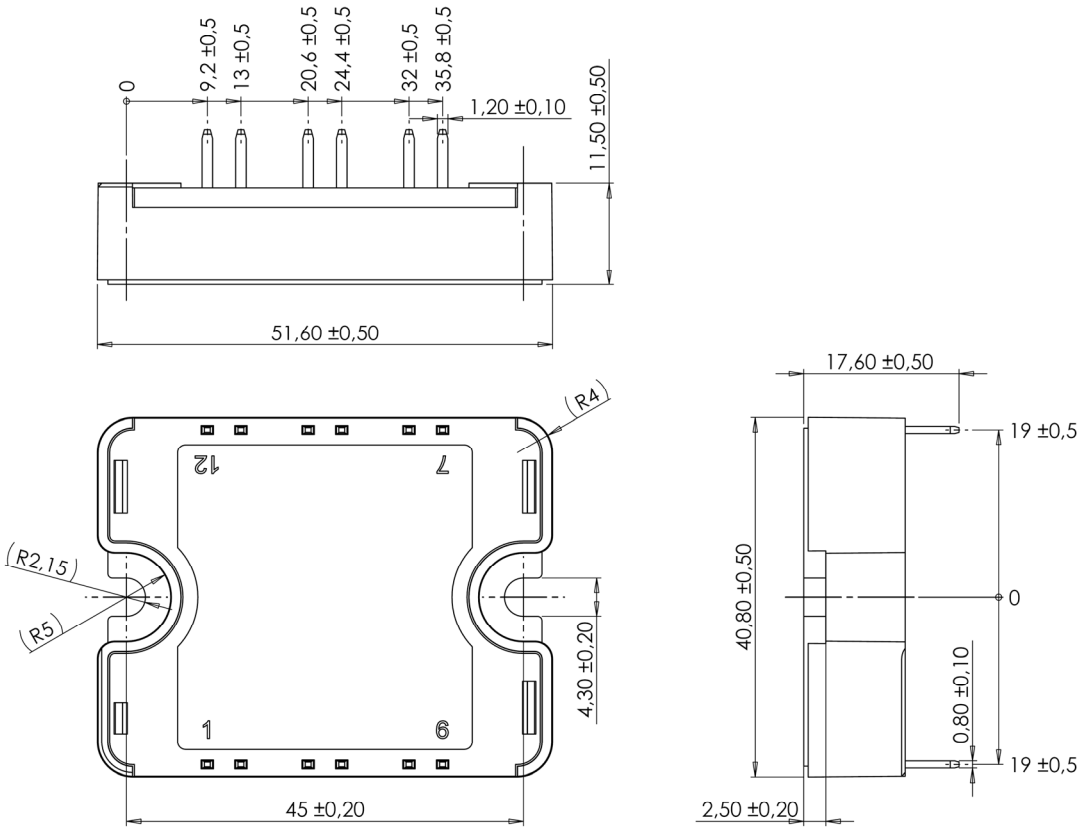
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		kΩ
$B_{25/85}$	T_{25} = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

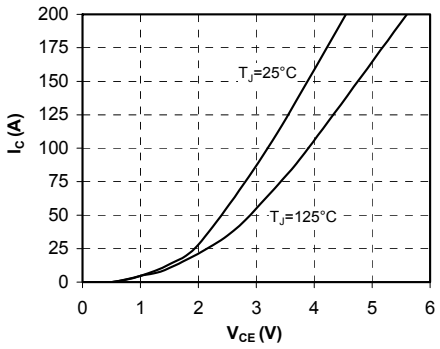
SP1 Package outline (dimensions in mm)



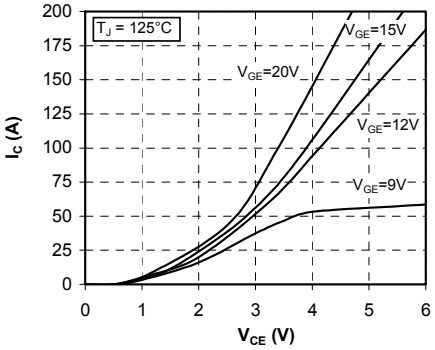
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical Performance Curve

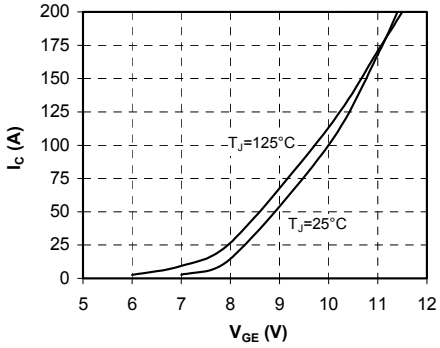
Output Characteristics (V_{GE}=15V)



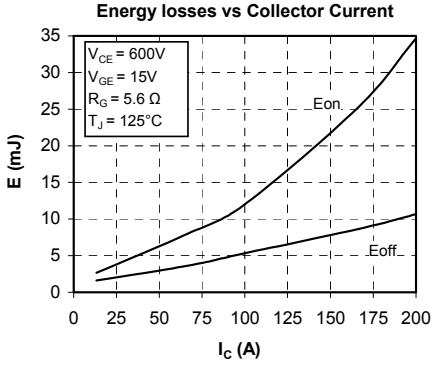
Output Characteristics



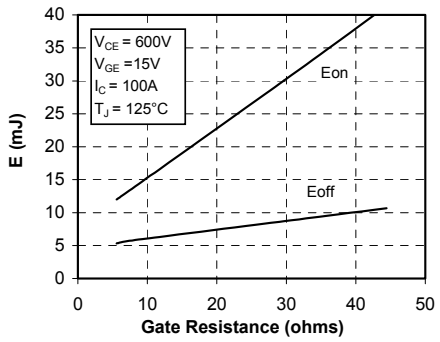
Transfert Characteristics



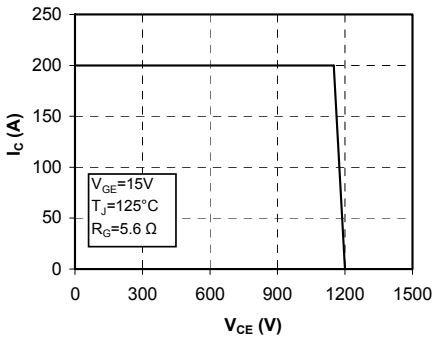
Energy losses vs Collector Current



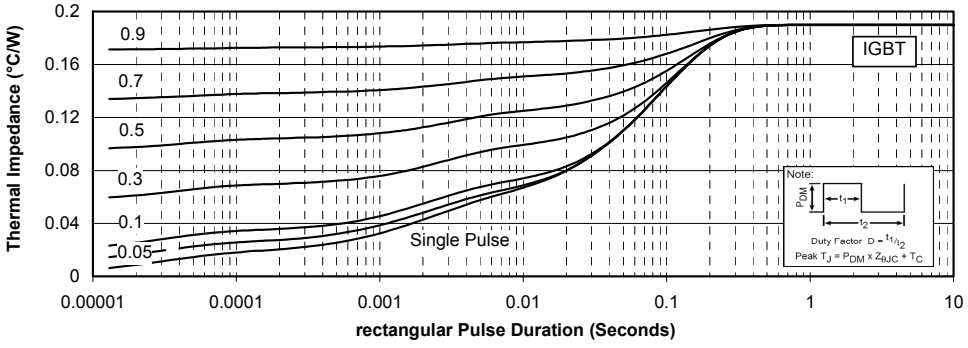
Switching Energy Losses vs Gate Resistance



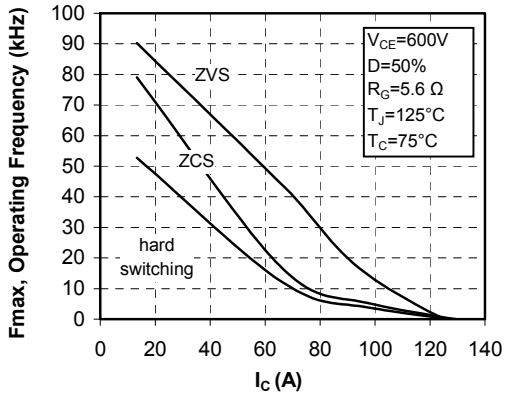
Reverse Bias Safe Operating Area



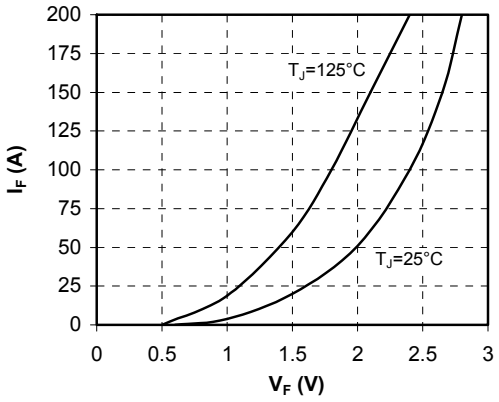
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



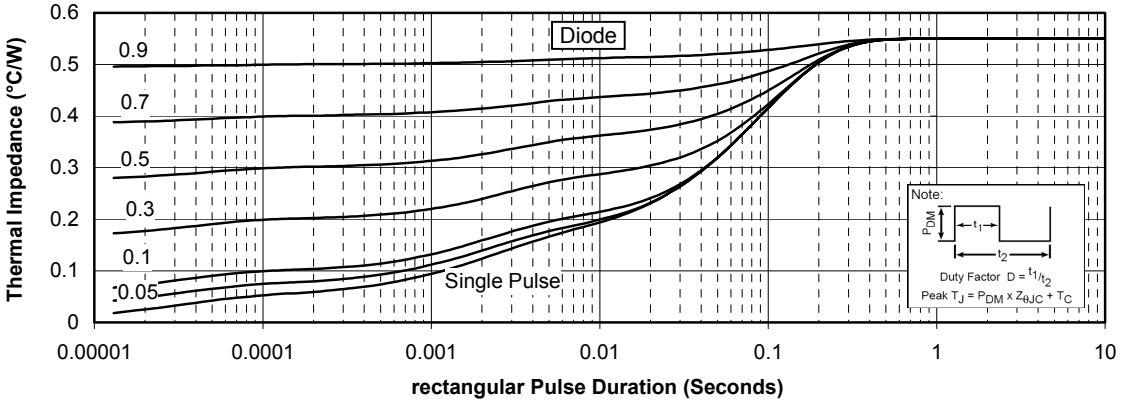
Operating Frequency vs Collector Current



Forward Characteristic of diode



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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